

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Complete If Known

Application Number	10/790,420
Filing Date	Concurrently Herewith
First Named Inventor	Jian Chen
Group Art Unit	2818
Examiner Name	
Attorney Docket Number	SC13210TP

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ Number ⁴ Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
HP	AJ	JP 2000243946	12/06/1999	Naoharu <i>et al.</i>		Yes/Abstract
HP	AK	WO 02/33746 A1	04/22/2002	Chu <i>et al.</i>		

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
HP	AL	Chi <i>et al.</i> , "Electrically active defects in surface preamorphized and subsequently RTP-annealed Si and the effect of titanium silicidation," <i>Proc. 1998 5th International Conference on Solid-State and Integrated Circuit Technology</i> , October 21, 1998, Beijing, China, p. 324-327.	
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	AO	LeGoues <i>et al.</i> , "Kinetics and Mechanism of Oxidation of SiGe: Dry Versus Wet Oxidation," <i>Applied Physics Letters</i> , February 13, 1989, Vol. 54, No. 7, pp. 644-646.	
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HP	AV	U.S. Patent Application S/N 10/670,928 filed 09/25/2003, entitled "SOI Template Layer", same assignee as assignee hereof.	

Examiner Signature	TU -TU HIO	Date Considered	June 2005
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